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Photoemission study of f-electron Heusler compound: UNiSn

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Using photoemission spectroscopy (PES), the electronic structures of XNiSn (X=Ce, U) have been investigated. The f-electron Heusler compound UNiSn displys an interesting multiple phase transition around 43K, and CeNiSn belongs to the low carrier density f-electron system that opens a gap at low temperature. It is found that the valence-band PES spectra of UNiSn and CeNiSn reveal some common features which are related to the Ce/U d, Ni d, and Sn sp electronic character. The Ni 3d spectrum shows the main peak well below the Fermi level E_F and a very low DOS at E_F in both compounds. We have found that the high-resolution photoemission spectra of both UNiSn and CeNiSn are described well by the V-shaped metallic DOS near E_F , which implies the reduced DOS at E_F and the semi-metallic ground electronic states. Our study suggests that the effect of the hybridization matrix element between the f electron orbitals and the very low Ni 3d DOS at E_F is important in both UNiSn and CeNiSn. The comparison of the LSDA+U calculation to the measured PES spectra reveals the importance of the on-site Coulomb interaction between f electrons.